

LISTING OF CLAIMS:

1. (Currently amended) A capacitive-type semiconductor sensor comprising:

a single semiconductor substrate;

a plurality of sensor chips formed on the single substrate and operable in respective single axes, each of the sensor chips having fixed electrodes and movable electrodes for producing a detection signal corresponding to capacitances between the fixed electrodes and the movable electrodes;

a shared ~~pad~~pad connected to the fixed electrodes of the plurality of ~~the~~ sensor chips and shared thereby; and

wirings connecting the fixed electrodes of the plurality of sensor chips and the shared ~~pads of the plurality of sensor chips~~pad, wherein the wirings are symmetrically formed with respect to wiring resistances from the shared pad to the fixed electrodes of the sensor chips.

2. (Original) The capacitive-type semiconductor sensor according to Claim 1, wherein two of the sensor chips are formed on the single substrate at an angle of 90 degrees to be operable in perpendicularly crossing directions.

3. (Original) The capacitive-type semiconductor sensor according to Claim 1, wherein two of the sensor chips are formed

on the single substrate in parallel with each other to be operable in reverse directions.

4. (New) A capacitive-type semiconductor sensor comprising:

a single semiconductor substrate;

first and second sensor chips formed on the single substrate and operable in respective single axes, each of the first and second sensor chips having first and second fixed electrodes and a movable electrode for producing a detection signal corresponding to capacitances between the first and second fixed electrodes and the movable electrode;

a first shared pad formed at a first position between the first and second sensor chips to be shared by the first and second sensor chips;

a second shared pad formed at a second position between the first and the second sensor chips to be shared by the first and second sensor chips;

a pair of first wirings connecting the first shared pad to the first fixed electrodes of the first and second sensor chips, respectively, each of the pair of first wirings being formed substantially symmetrically with respect to each other to have substantially the same wiring resistances; and

a pair of second wirings connecting the second shared pad

to the second fixed electrodes of the first and second sensor chips, respectively, each of the pair of second wirings being formed substantially symmetrically with respect to each other to have substantially the same wiring resistances.

5. (New) The capacitive-type semiconductor sensor according to Claim 4, wherein the first and second sensor chips are formed on the single substrate at an angle of 90 degrees to be operable in perpendicularly crossing directions.

6. (New) The capacitive-type semiconductor sensor according to Claim 4, wherein the first and second sensor chips are formed on the single substrate in parallel with each other to be operable in reverse directions.